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- (71) Applicant: EPCOS AG [DE/DE]; St.-Martin-Str. 53, 81669 München (DE).
- (72) Inventors: YOON, Jiman; Kohlergasse 10, 86152 Augsburg (DE). MAYER, Markus; Akeleistr. 10, 82024 Taufkirchen (DE). EBNER, Thomas; Hunkelestr. 12, 81476 München (DE). RÖSLER, Ulrike; Weichselweg 9, 85241 Hebertshausen (DE). RUILE, Werner; Klarastr. 5 a, 80636 München (DE).
- (74) Agent: EPPING HERMANN FISCHER PATENTANWALTSGESELLSCHAFT MBH; Schlossschmidstr. 5, 80639 Munich (DE).

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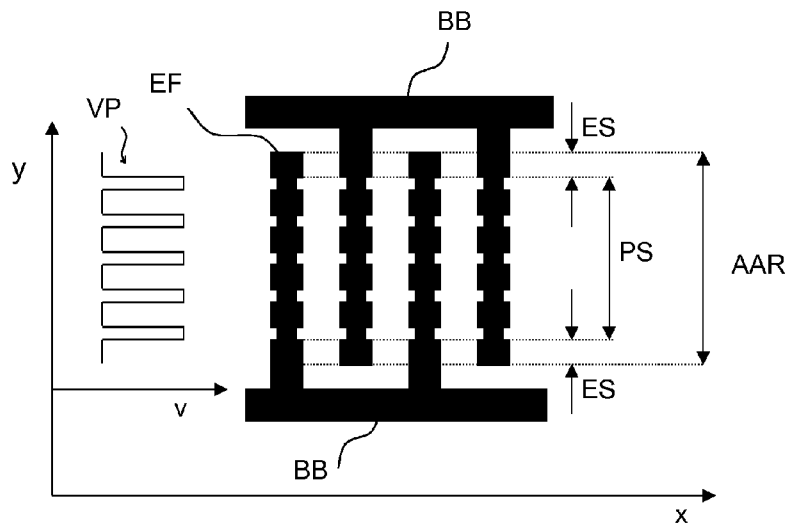


Fig. 4

(57) Abstract: An improved electroacoustic transducer with an improved mode profile (VP) is provided. The transducer comprises a velocity profile with a periodic structure (PS) and an edge structure (ES) flanking the periodic structure. The velocity profile also allows to suppress the SH wave mode.

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Description

Electroacoustic transducer with improved suppression of unwanted modes

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The present invention refers to electroacoustic transducers with improved profiles of the acoustical wave mode.

Electroacoustic transducers may be used in RF filters working with acoustical waves. An according filter can comprise one or more electroacoustic resonators in one or more acoustic tracks. The resonators comprise transducers with interdigitating electrode fingers, each of which is connected to one of two busbars of the transducer. Utilizing the piezoelectric effect the transducer converts an electromagnetic RF signal into acoustic waves and vice versa.

Possible implementations of electroacoustic transducers are SAW transducers (SAW = Surface Acoustic Wave) or GBAW transducers (GBAW = Guided Bulk Acoustic Wave).

If unwanted wave modes are not suppressed in resonators the electrical properties of respective RF filters are deteriorated.

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From EP 1 871 006 A1 and from EP 1 962 424 A1 SAW transducers are known. Aperture weighting is used to suppress unwanted transversal modes.

From US 7,576,471 B1, US 2013/051588 A1 and from US 7,538,637 B2 transducers operating in a piston mode are known to suppress unwanted transversal modes.

From US 7,939,987 B1 further means such as two dimensional reflectors are known to suppress transversal modes.

5 From the article "Two Dimensional Periodic Array of Reflection Centers on Electrodes in SAW Resonators" (Jiman Yoon et al., Ultrasonic Symposium, 2012, IEEE, Oct 2012, p. 1798 - 1801) means for shaping the fundamental mode in a transducer are known.

10 However, spurious modes such as SH modes (SH = Shear Horizontal) also lead to deterioration of the electrical properties of RF filters.

15 It is, thus, an object to provide an electroacoustic transducer allows improved electrical properties of respective filters. In particular, it is an object to provide a transducer in which both, transversal modes and SH modes are sufficiently suppressed.

20 For this purpose, electroacoustic transducers according to the independent claims are provided. The dependent claims provide preferred embodiments of the invention.

25 Two transducers schemes are presented: One for transducers with LiNbO_3 as the piezoelectric material and one for transducers with LiTaO_3 as the piezoelectric material.

30 An electroacoustic transducer with LiNbO_3 as the piezoelectric material comprises a longitudinal direction and a transversal direction orthogonal to the longitudinal direction. The longitudinal direction defines the main propagation direction of the acoustic waves. The transversal direction

mainly defines the orientation of electrode fingers of the transducer.

The transducer further comprises a transversal velocity profile of acoustic waves propagating in the transducer and an acoustically active region. The acoustically active region is mainly defined as the overlap region of electrode fingers of opposite polarity, i.e. as the area in which acoustic waves propagating in the longitudinal direction are excited when an RF signal is applied to the transducer.

The transversal velocity profile has a periodic structure in this active region. The periodic structure has a plurality of minimal values and a plurality of maximal values larger than the minimal values. Further, the periodic structure is flanked on both sides by an edge structure of the transversal velocity profile. The velocity in the edge structure is lower than the maximal values of the periodic structure.

It is possible that the periodic structure has two outermost sections with a maximum velocity.

I.e. there are two stripes of a lower velocity per unit cell arranged next to the periodic structure within the active region. Here, the unit cell denotes a segment of the acoustic track with a length in the longitudinal direction of the acoustic wavelength λ .

An electroacoustic transducer with LiTaO_3 as the piezoelectric material comprises a longitudinal direction and a transversal direction orthogonal to the longitudinal direction. The longitudinal direction defines the main propagation direction of the acoustic waves. The transversal direction

mainly defines the orientation of electrode fingers of the transducer.

The transducer further comprises a transversal velocity profile of acoustic waves propagating in the transducer and an acoustically active region. The acoustically active region is mainly defined as the overlap region of electrode fingers of opposite polarity, i.e. as the area in which acoustic waves propagating in the longitudinal direction are excited when an RF signal is applied to the transducer.

The transversal velocity profile has a periodic structure in this active region. The periodic structure has a plurality of minimal values and a plurality of maximal values larger than the minimal values. Further, the periodic structure is flanked on both sides by an edge structure of the transversal velocity profile. The velocity in the edge structure is higher than the minimal values of the periodic structure.

It is possible that the periodic structure has two outermost sections with a minimum velocity.

I.e. there are two stripes of a higher velocity in each unit cell arranged next to the periodic structure within the active region.

Especially in transducers with LiTaO_3 being the piezoelectric substrate the presence of dummy fingers may be preferred.

The two stripes per unit cell can extend over the length of the transducer resulting in a total number of two stripes per transducer.

The velocity profile can be a $\Delta v/v$ waveguide. I. e. the periodic structure can be a part of $\Delta v/v$ waveguide.

5 The periodic structure and the edge structure establish a region of stripes of chosen velocity values extending in the longitudinal direction.

The wording "periodic structure" denotes the shape of the velocity profile in the transversal direction. In the periodic
10 structure the velocity profile, thus, comprises identical sections of higher and lower velocity being arranged next to one another and extending in the transversal direction.

The periodic structure can consist of a sinusoidal structure,
15 a saw tooth structure, a square-wave structure. However, the periodic structure can be built-up of a combination of these structures.

It is possible that the periodic structure has a periodicity
20 in the periodic length but the amplitude of minimum and maximum velocity values follow a profile, e. g. a parabola, sine function or a cosine function.

It was found that the combination of the periodic structure
25 and the edge structure define a velocity profile in the active region of a transducer in which not only unwanted transversal modes but also SH modes are effectively suppressed or even eliminated. This is surprising as conventional means
30 only can suppress one of two or more unwanted modes, i.e., only unwanted transversal modes, and reduce the efficiency of the transducer.

In one embodiment the edge structure comprises two stripes per unit cell being arranged directly next to a respective side of the periodic structure. Thus, the edge structure directly flanks the periodic structure with no other section in
5 between.

In principle, the length of the edge structure is not limited to the periodic length of the periodic structure. The length can be larger than the periodic length or smaller than the
10 periodic length. However, in one embodiment, especially working with LiNbO_3 as the piezoelectric material, the edge structure has a length l being larger than 50 % of a period, i.e. the periodic length, of the periodic structure.

15 In one embodiment, especially working with LiTaO_3 as the piezoelectric material, the edge structure has a length l being smaller than 50 % of a period, i.e. the periodic length, of the periodic structure.

20 The phrase "length" when referred to the transducer itself means the extension in the longitudinal direction. The phrase "width" when referred to the transducer itself means the extension in the transversal direction.

25 The phrase "length" when referred to an electrode finger or to the velocity profile means the extension in the transversal direction. The phrase "width" when referred to an electrode finger or to the velocity profile means the extension in the longitudinal direction.

30

In one embodiment the transducer further comprises one stripe of a gap structure per unit cell flanking the edge structure. the number of electrode fingers per unit cell In the acousti-

cally active region is twice the number of the electrode fingers in the gap region. Thus, only one stripe of the gap structure exists in each unit cell. In the gap structure the velocity is larger than the maximal value of the periodic structure. The active region is arranged between the longitudinal sections of the gap structure, i.e. the gap structure is not a part of the active region.

It is possible that the gap structure corresponds to an area of piezoelectric material of the transducer where the ends of electrode fingers of one polarity oppose elements, e.g. the busbar itself or dummy fingers connected to the busbar, of the respective other electrode.

In one embodiment the gap structure's stripes have a length from 0.5λ to 10λ or, especially, from 2λ to 4λ . Here, the phrase "length" denotes the extension along the transversal direction.

Here, λ denotes the wavelength of the wanted acoustic waves propagating in the longitudinal direction. The wavelength λ is mainly defined by the periodic length of the finger structure, e.g. of the average periodic length, of the transducer.

The gap structure can be flanked by structures of reduced velocity. The reduction of the velocity may be caused by an increase of the finger width or by the mass loading which may be achieved by an additional metal layer.

In one embodiment the gap structure has a metallization ratio η between 0.2 and 0.8. The metallization ratio η is defined as

$$\eta = (w_1 + w_2 + \dots + w_n) / \lambda$$

where w_i denotes the width of the i -th electrode finger of electrode fingers within a distance of length λ along the longitudinal direction. In a conventional transducer in the active region n equals 2. In a splitfinger transducer n may equal 4. In the region of the acoustic track corresponding to the gap structure only electrode fingers of one polarity may be present. Thus, n may equal 1.

10 In one embodiment the transducer comprises a piezoelectric substrate, two busbars arranged on the substrate and aligned parallel to the longitudinal direction and interdigitated electrode fingers. The fingers are arranged on the substrate, connected to one of the busbars, and aligned parallel to the transversal direction.

The overlap of fingers of opposite polarity defines the active region.

20 The presence of the electrode fingers on the substrate establish a convenient way to shape the velocity profile: With the mass of the fingers, the fingers acoustic impedance and electric resistivity details of the wave propagation, especially the wave velocity, can be manipulated. Increasing the mass loading of the substrate at a place of the substrate - e.g. via material of the electrode structure of the busbars and electrode fingers - mainly leads to a decrease of the wave velocity. Increasing the stiffness parameters of the acoustic track - e.g. via a material with a high Young's Modulus - mainly leads to an increase of the velocity.

30 In one embodiment, accordingly, the transversal velocity profile is adjusted via one or more measures selected from:

- reduced velocity by increased mass loading by increased finger width,
- reduced velocity by increased mass loading by increased finger thickness,
- 5 - reduced velocity by increased mass loading by additional material deposited on the electrode fingers,
- reduced velocity in the gap region by increased mass loading by dummy patches in the gap region,
- reduced velocity by increased mass loading by material deposited in stripes on the electrode fingers,
- 10 - increased velocity by reduced mass loading by reduced finger width,
- increased velocity by reduced mass loading by reduced finger thickness,
- 15 - increased velocity by reduced mass loading by material removed from the electrode fingers.

The metallization ratio η in regions of a lower velocity can be in the range from 0.3 to 0.8. Values between 0.4 and 0.75
20 may be preferred.

The metallization ratio η in regions of a higher velocity can be in the range from 0.15 to 0.75. Values between 0.2 and 0.6
25 may be preferred.

The periodic length in the periodic structure can be in the range from 0.2 to 3λ , λ being the acoustic wavelength (in the longitudinal direction).

30 The ratio between the length of the higher velocity divided by the periodic length can be in the range from 0.2 to 0.8. A ratio between 0.4 and 0.6 may be preferred.

For LiNbO₃ substrates the following is true: The length of the sections of the edge structure may be in the range from 0.2 λ to 3 λ . Lengths between 0.3 λ and 2.5 λ may be preferred.

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For LiTaO₃ substrates the following is true: The length of the sections of the edge structure may be in the range from 0.1 λ to 1 λ . Lengths between 0.2 λ and 0.7 λ may be preferred.

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It is possible that the transversal velocity profile comprises further periodic or aperiodic or symmetric or asymmetric structure. However, it is also possible that the transversal velocity profile in the acoustic track consists of the above mentioned structures.

15

With an transducer as described above the normalized overlap integral $\langle \Phi | \Psi_n \rangle$ for the fundamental mode $n = 1$ can be in the range of 0.95 or above. As the overlap integral describes the match between the (normalized) excitation function Φ and the (normalized) wave mode shape Ψ_n and as the different modes Ψ_n are orthogonal a value just below 1 prevents higher modes to be excited.

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25 Brief description of the figures

The transducer is explained in greater detail on the basis of exemplary and not limiting embodiments and associated figures below.

30

Fig. 1 shows the orientation of the longitudinal direction x with respect to the transversal direction y .

Fig. 2 shows the transversal velocity profile v along the transversal direction y .

5 Fig. 3 shows the orientation of the transducer with respect to the longitudinal direction x and the transversal direction y .

10 Fig. 4 illustrates a possible causal connection between the velocity profile and a physical realization of the transducer's electrode structure.

15 FIG. 5 shows the conductance of the transducer as described above compared to the conductance of conventional transducers.

FIG. 6 shows the velocity profile and the profile of the fundamental mode of the improved transducer the conductance of which is shown in FIG. 5.

20 FIG. 7 shows the velocity profile of the second symmetric wave mode of an embodiment of the transducer together with the mode profile and the absolute value of the mode profile.

25 FIG. 8 shows the velocity profile and the respective mode profile and its absolute value of the third symmetric wave mode.

30 FIG. 9 shows the velocity profile and the respective mode profile and its absolute value of the fourth symmetric wave mode.

- FIG. 10 shows the velocity profile and the mode profile and its respective absolute value of the fifth symmetric wave mode.
- 5 FIG. 11 shows the frequency-dependent conductance of a transducer with a 2D periodic array with patches compared to the conductance of a conventional transducer.
- 10 FIG. 12 shows the velocity profile and the wave mode and its respective absolute value of the transducer having the frequency characteristic shown in FIG. 11.
- 15 FIG. 13 shows an embodiment of a transducer's electrode structure.
- FIG. 14 shows another embodiment of an electrode structure having an increased finger width in a region corresponding to the gap structure.
- 20 FIG. 15 shows an embodiment of electrode structures having a reduced finger width in the region corresponding to the gap structure.
- 25 FIG. 16 shows an embodiment of electrode structures comprising dummy finger patches arranged within the region corresponding to the gap structure.
- 30 FIG. 17 shows stripes comprising a dielectric material arranged in the region corresponding to the gap structure.

FIG. 18 shows an embodiment of electrode structures comprising metal bars arranged on a dielectric material arranged on the electrode fingers and the bus bars.

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FIG. 19 shows an embodiment of a transducer structure where material is removed in the active region to reduce the mass loading.

10 FIG. 20 shows an embodiment of a transducer structure with individual additional masses arranged on each side of the electrode fingers to increase the mass loading.

15 FIG. 21 shows electrode structures the material of which is partially removed to obtain the respective velocity profile.

20 FIG. 22 shows an embodiment of electrode structures with additional material deposited on locally etched electrode structures.

FIG. 23 shows electrode fingers with recesses.

25 FIG. 24 shows electrode structures with additional metal bars in the region correlated to the gap structure and with recesses in the electrode fingers establishing the periodic structure.

30 Detailed description

FIG. 1 shows a substrate SU which may comprise piezoelectric material such as lithium niobate (LiNbO_3) or lithium tanta-

late (LiTaO_3). x denotes the longitudinal direction. y denotes the transversal direction. Interdigital transducers are arranged in such a way that the main direction of propagation is parallel to the x -direction. Accordingly, a crystal cut of the substrate SU is chosen to obtain a high coupling coefficient.

FIG. 2 illustrates the velocity profile VP of acoustic waves propagating in the substrate SU shown in FIG. 1. The velocity profile has a periodic structure PS which is flanked by edge structures ES in such a way that the periodic structure PS is arranged between the edge structures ES in the transversal direction y . The periodic structure PS comprises areas with a relative high velocity v and areas with a relative low velocity. The areas of high and low velocity alternate in such a way that a periodic velocity profile in the periodic structure is obtained. The velocity in the edge structure is lower than the maximum velocity in the periodic structure PS.

The velocity in the edge structure may be equal to the lowest velocity in the periodic structure. However, the velocity in the edge structure ES may differ from the lowest velocity in the periodic structure. Also, the length of the edge structure is not limited. However, it may be preferred that the length of the respective stripe of the edge structure ES is larger than half of the periodic length of the periodic structure PS. Here the phrase "length" denotes the extension of the edge structure in the transversal direction.

FIG. 3 shows the orientation of the transducer TD comprising bus bars BB and electrode fingers EF with respect to the longitudinal direction x and the transversal direction y . The area in which the electrode fingers of opposite electrodes

overlap is called the acoustically active region AAR. The bus bars are oriented parallel to the longitudinal direction x . The electrode fingers EF are oriented parallel to the transversal direction y .

5

When an RF signal is applied to the bus bars and the bus bars have opposite polarities, an acoustic wave is excited in the piezoelectric substrate SU.

10 FIG. 4 shows the connection of the electrode structure and the velocity profile v . The velocity of acoustic waves at the surface or an interface of a piezoelectric material depends on the mass loading at the interface. A higher mass loading and/or a higher reflection decreases the velocity. However,
15 higher elastic constants of a material deposited on the piezoelectric material increases the velocity. Thus, the shape of the velocity profile v along the transversal direction y can directly depend on geometric structures of the material arranged on the piezoelectric substrate, e.g. the electrode
20 structures comprising the bus bars BB and the electrode fingers EF. To obtain the periodic structure of the velocity profile VP, the electrode fingers EF may have a shape with a corresponding periodic symmetry. To obtain minima in the velocity profile, the local finger width can be increased compared to sections where the velocity should be maximal and
25 the according finger width is, thus, reduced. Further, in order to obtain the edge structure with a reduced velocity compared to the maximal velocity within the periodic structure, the finger width can be larger in the area corresponding to
30 the edge structure compared to the area corresponding to the highest velocities in the periodic structure.

FIG. 5 shows the conductance curves of two transducers. The frequency-dependent conductance of a conventional transducer is denoted as "1" while the conductance of an improved transducer is denoted as "2". Especially at a frequency of approximately 910 MHz, the conventional transducer offers a peak deriving from the SH mode. A resonance in the improved transducer is efficiently suppressed.

The transducer, of which the frequency-dependent conductance is shown in FIG. 5, has a velocity profile shown in FIG. 6. The velocity profile VP has a periodic structure between two structures deviating from the periodic structure, namely the edge structure ES. In the velocity profile VP shown in FIG. 6, the fundamental mode FM is formed. The combination of the periodic structure and the edge structure ES allows to efficiently suppress the SH mode while also no or nearly no transversal modes are excited.

FIG. 7 shows a velocity profile and the corresponding symmetric wave mode profile together with its absolute value. As can be seen, the amplitude of the mode profile with a positive displacement is mainly equal to the amplitude of the mode profile with a negative displacement in the periodic structure. Thus, the areas of positive and negative displacements, i.e. the value of the integral of the mode profile mainly vanishes and the excitation strength of the second symmetric mode is minimized.

FIG. 8 shows, similar to the situation shown in FIG. 7, the mode profile and its absolute value of the velocity profile already shown in FIG. 7. Again, the amplitude of positive and negative displacements are mainly equal. Thus, the excitation strength of the third symmetric mode profile is minimized.

FIG. 9 shows the mode profile of the fourth symmetric wave mode. Again, the amplitude of positive and negative displacements are mainly equal. Thus, the excitation strength of the fourth symmetric wave mode is minimized.

5

FIG. 10 shows the mode profile and its absolute value of the fifth symmetric wave mode. Again, the excitation strength is minimized as the shape of the velocity structure with the edge structure flanking the periodic structure is an efficient means to suppress higher order modes.

10

FIG. 11 shows conductance curves of a conventional transducer, curve "1" and of a transducer where the velocity in the edge structure is equal to the highest velocity in the periodic structure, curve "2". Further, the velocity in the periodic structure or in the active region (the velocity profile is shown in FIG. 12) is very slow so that the transversal mode, of which the wavelength is equal or similar to the transversal periodicity, is bounded. As a result, a plurality of resonances in the frequency-dependent conductance - as shown by curve 2 - are obtained.

15

20

FIG. 12 shows the velocity profile corresponding to conductance curve 2 of FIG. 11. Since the transversal mode is bounded, the shape of the mode profile becomes cosine-like. A comparison between the mode profile shown in FIG. 12 and the absolute value of the mode profile reveals that the negative displacement has a smaller amplitude than the positive displacement. As a result, the signal is not cancelled out completely and the plurality of resonances shown in FIG. 11 are obtained.

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Thus, the depth of the velocity profile should not exceed critical values. The waveguide parameters have to be chosen in such a way that the highest bounded mode has a lower number than the mode responsible for the second resonances as shown in curve 2 of FIG. 11.

The highest bounded mode - denoted as n_{\max} - that a wave guide can contain is a function of the aperture and the track and gap velocity:

10

$$n_{\max} = 2 A f_0 \text{ sqrt } [1/(v_{\text{track}})^2 - 1/(v_{\text{gap}})^2]$$

Here, A denotes the aperture. f_0 denotes the resonance frequency, V_{track} is the lowest velocity in the active region.

15 V_{gap} is the velocity in the gap structure.

FIG. 13 shows a basic embodiment where the periodic structure of the velocity profile is obtained by an according periodic finger width variation in the electrodes.

20

FIG. 14 is an embodiment of a transducer where a reduced velocity in the gap structure is obtained by an increase of the finger width of the electrodes in the area corresponding to the gap structure.

25

FIG. 15 shows an embodiment of a transducer structure where the velocity in the gap structure is increased by a reduced finger width in the corresponding section of the electrodes.

30

FIG. 16 shows an embodiment where mass loading is increased to reduce the velocity in the gap structure by additional dummy fingers arranged in such a way that the distance be-

tween the bus bar and an electrode finger is reduced to a minimum.

FIG. 17 shows an embodiment of a transducer where a dielectric material, e.g. comprising a silicon dioxide, is arranged in two stripes in the gap structure corresponding region.

FIG. 18 shows an embodiment of a transducer where the electrode fingers are covered with a dielectric material, e.g. silicon dioxide. The left part of FIG. 18 shows a top view onto the transducer where two stripes of metal increase the mass loading to reduce the velocity in the gap structure corresponding region. The right part of FIG. 18 shows a cross-section through the transducer showing that the dielectric material is arranged between the metal stripes and the electrodes.

As a dielectric material DS is arranged between the electrode fingers EF and the stripes for increased mass loading MS, the stripes MS can comprise a metal. This is in contrast to FIG. 17 where the stripes are directly arranged on the electrode fingers. Thus, an insulating material is preferred in the embodiment shown in FIG. 17.

FIG. 19 shows on the left-hand side a top view onto a transducer structure and the thickness of the respective metallization of the electrode fingers along the transversal direction (right-hand side). In the active region, the thickness of the metallization is reduced. In the region corresponding to the gap structure, the thickness is larger than in the active region. Thus, a velocity profile in which the velocity in the gap structure is reduced compared to the periodic structure is obtained.

FIG. 20 shows an embodiment of a transducer where the transducer structure is covered with a dielectric material DM. In order to increase the mass loading, individual segments of a material with a high density, e.g. a metal, are arranged on the respective electrode fingers of the edge structure. As the additional material is arranged directly on the electrode material and not isolated from the electrodes via the dielectric material DM, the segments of the additional material should not be in direct contact with each other.

10

FIG. 21 shows an important aspect in forming the velocity profile shown in the upper right part of FIG. 21: The lower part of FIG. 21 shows that the height of the metallization establishing the electrode fingers can be varied along the transversal direction to adjust the velocity profile. A periodic profile can be etched into the electrode finger to obtain the periodic structure PS. The thicknesses in the regions corresponding to the edge structures and the gap structures can be adjusted accordingly.

20

FIG. 22 shows a further embodiment of the transducer shown in FIG. 21 where further to the etching to obtain different thicknesses in the electrode structure, a dielectric, e.g. a silicon dioxide, is arranged on the electrode structures. Further, another material is deposited in stripes in the gap regions to adjust the velocity profile.

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FIG. 23 shows an embodiment where recesses are structured into the electrode fingers to provide a physical basis for the periodic structure of the velocity profile.

30

FIG. 24 shows further to the recesses of FIG. 23 in the electrode fingers material bars, e.g. metal bars, in the areas

corresponding to the gap structure as a physical realization of the velocity setting.

List of reference symbols:

	1, 2:	frequency-dependent conductance of a transducer
	AAR:	acoustically active region
5	BB:	bus bar
	DM:	dielectric material
	DS:	dielectric stripe
	EF:	electrode finger
	ES:	edge structure
10	FM:	frequency modulation
	GS:	gap structure
	MS:	metallic stripe
	PS:	periodic structure
	SU:	substrate
15	TD:	transducer
	v:	velocity
	VP:	velocity profile
	x:	longitudinal direction
	y:	transversal direction

Claims:

1. An electroacoustic transducer (TD), comprising
- a longitudinal direction (x) and a transversal direction
 - 5 (y) orthogonal to the longitudinal direction (x),
 - a transversal velocity profile (VP) of acoustic waves propagating in the transducer (TD),
 - an acoustically active region (AAR),
- wherein
- 10 - the transversal velocity profile (VP) has a periodic structure (PS) in the active region (AAR),
 - the periodic structure (PS) has a plurality of minimal values and a plurality of maximal values larger than the minimal values,
 - 15 - the periodic structure (PS) is flanked on both sides by an edge structure (ES) of the transversal velocity profile (VP), the velocity (v) in the edge structure (ES) being lower than the maximal values of the periodic structure (PS),
 - 20 - the piezoelectric material is LiNbO_3 .
2. An electroacoustic transducer (TD), comprising
- a longitudinal direction (x) and a transversal direction
 - (y) orthogonal to the longitudinal direction (x),
 - 25 - a transversal velocity profile (VP) of acoustic waves propagating in the transducer (TD),
 - an acoustically active region (AAR),
- wherein
- the transversal velocity profile (VP) has a periodic
 - 30 structure (PS) in the active region (AAR),
 - the periodic structure (PS) has a plurality of minimal values and a plurality of maximal values larger than the minimal values,

- the periodic structure (PS) is flanked on both sides by an edge structure (ES) of the transversal velocity profile (VP), the velocity (v) in the edge structure (ES) being higher than the minimal values of the periodic structure (PS),
- the piezoelectric material is LiTaO_3 .

3. The transducer (TD) of the previous claim comprising dummy fingers.

4. The transducer (TD) of one of the previous claims, where the edge structure (ES) comprises two stripes per unit cell, each of the two stripes being arranged directly next to a respective side of the periodic structure (PS).

5. The transducer (TD) of claim 4, where the stripes of the edge structure (ES) have a length l being larger than 50 % of a periodic length of the periodic structure (PS).

6. The transducer of claim 4, where the stripes of the edge structure have a length l being smaller than 50 % of a periodic length of the periodic structure (PS).

7. The transducer (TD) of the one of the previous claims, comprising

- two stripes of a gap structure (GS)

where

- in the gap structure (GS) the velocity (v) is larger than the maximal value of the velocity (v) of the periodic structure (PS),

- the active region (AAR) is arranged between the two stripes of the gap structure (GS).

8. The transducer (TD) of the previous claim, where the gap structure's (GS) stripes have a length from 0.5λ to 10λ or from 2λ to 4λ .

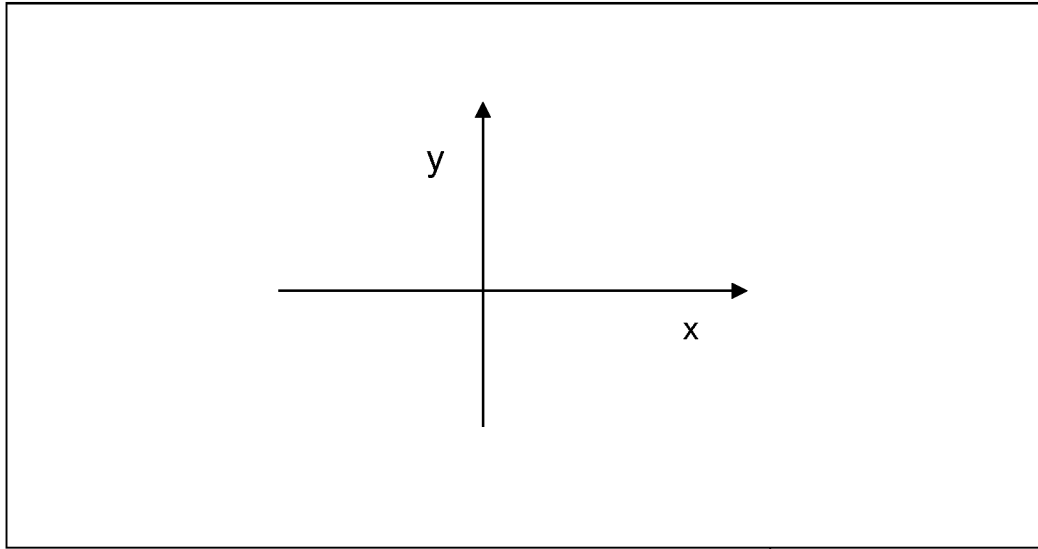
5 9. The transducer (TD) of one the two previous claims, where the gap structure (GS) has a metallization ratio η from 0.2 to 0.8.

10 10. The transducer (TD) of one of the previous claim,
comprising
- a piezoelectric substrate (SU),
- two busbars (BB) arranged on the substrate (SU) and aligned parallel to the longitudinal direction (x),
- interdigitated electrode fingers (EF), each arranged on the
15 substrate (SU), connected to one of the busbars (BB), and aligned parallel to the transversal direction (y).

11. The transducer (TD) of one of the previous claims, where the transversal velocity profile (VP) is adjusted via one
20 or more measures selected from:
- reduced velocity (v) by increased mass loading by increased finger (EF) width,
- reduced velocity (v) by increased mass loading by increased finger (EF) thickness,
25 - reduced velocity (v) by increased mass loading by additional material deposited on the electrode fingers (EF),
- reduced velocity (v) in the gap structure (GS) by increased mass loading by dummy patches in a gap region corresponding
30 to the gap structure (GS),
- reduced velocity (v) by increased mass loading by material deposited in stripes on the electrode fingers (EF),

- 26 -

- increased velocity (v) by reduced mass loading by reduced finger (EF) width,
- increased velocity (v) by reduced mass loading by reduced finger (EF) thickness,
- 5 - increased velocity (v) by reduced mass loading by material removed from the electrode fingers (EF).



SU

Fig. 1

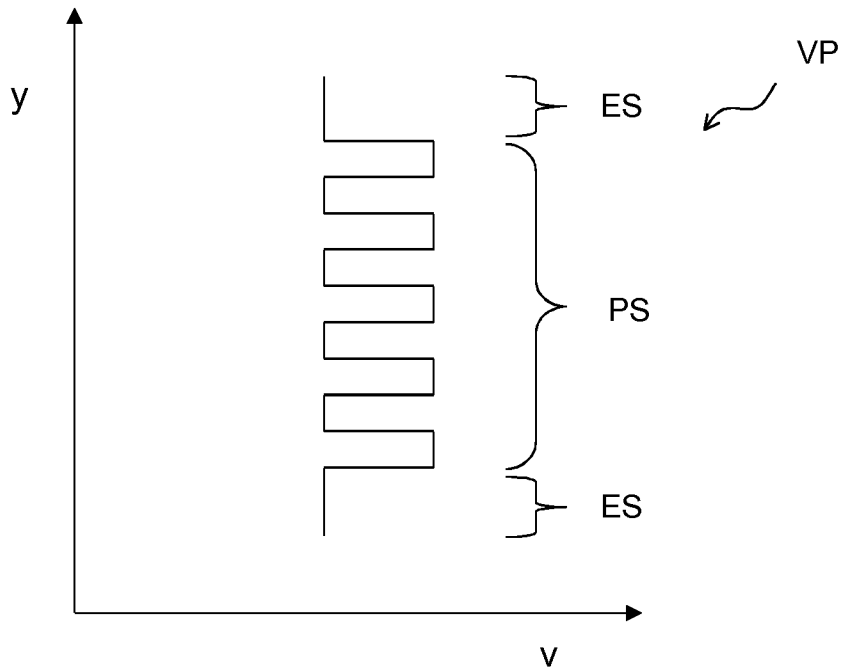
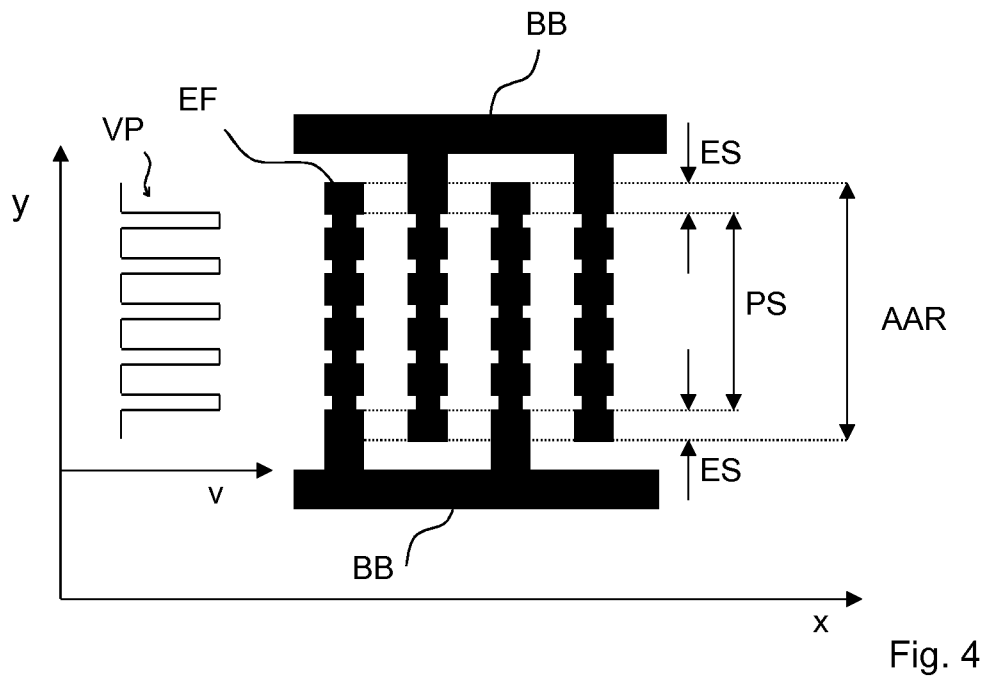
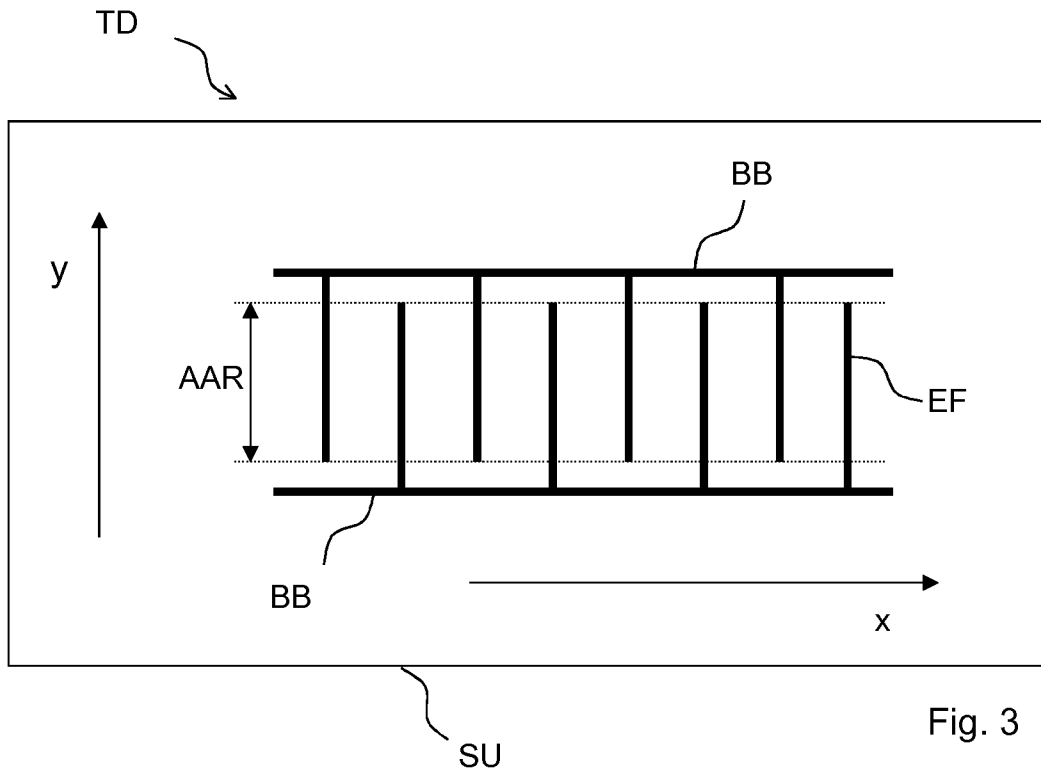


Fig. 2



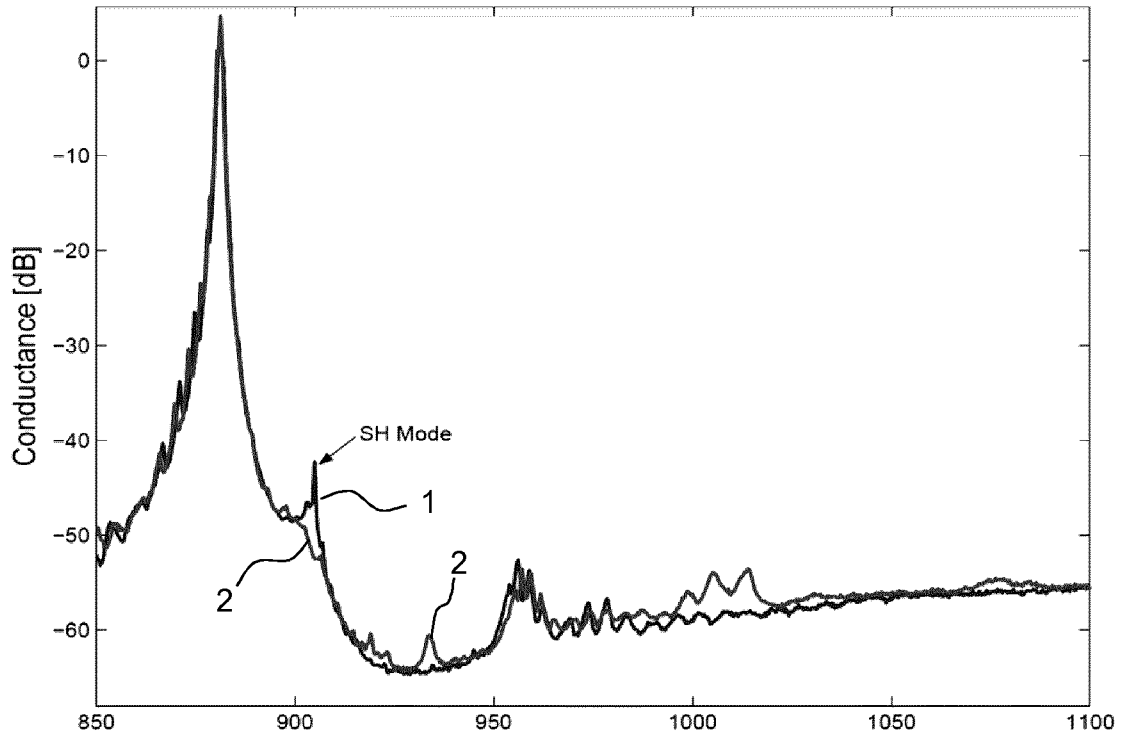


Fig. 5

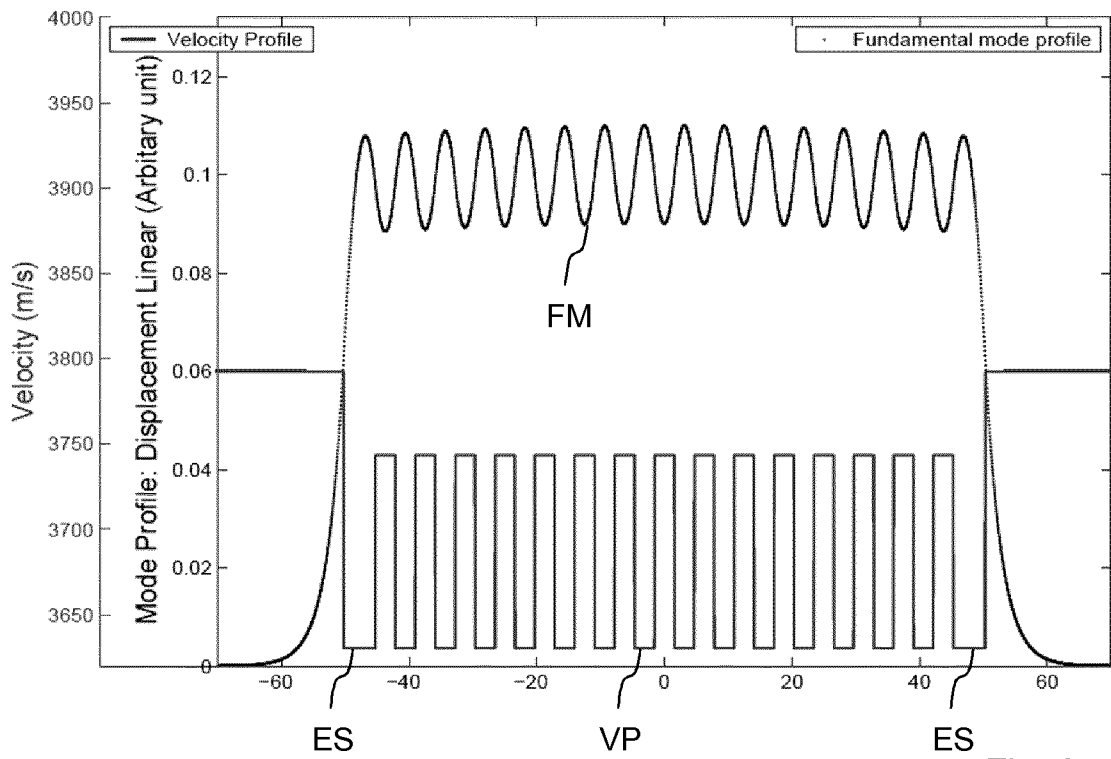


Fig. 6

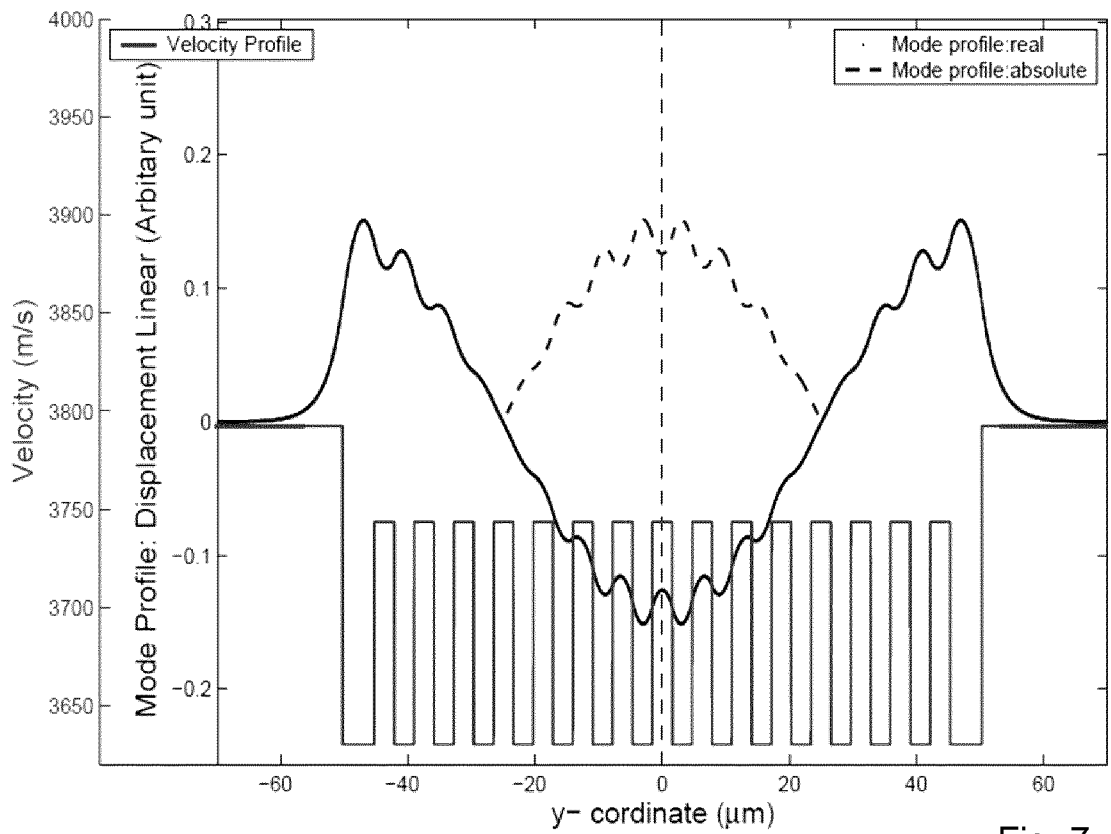


Fig. 7

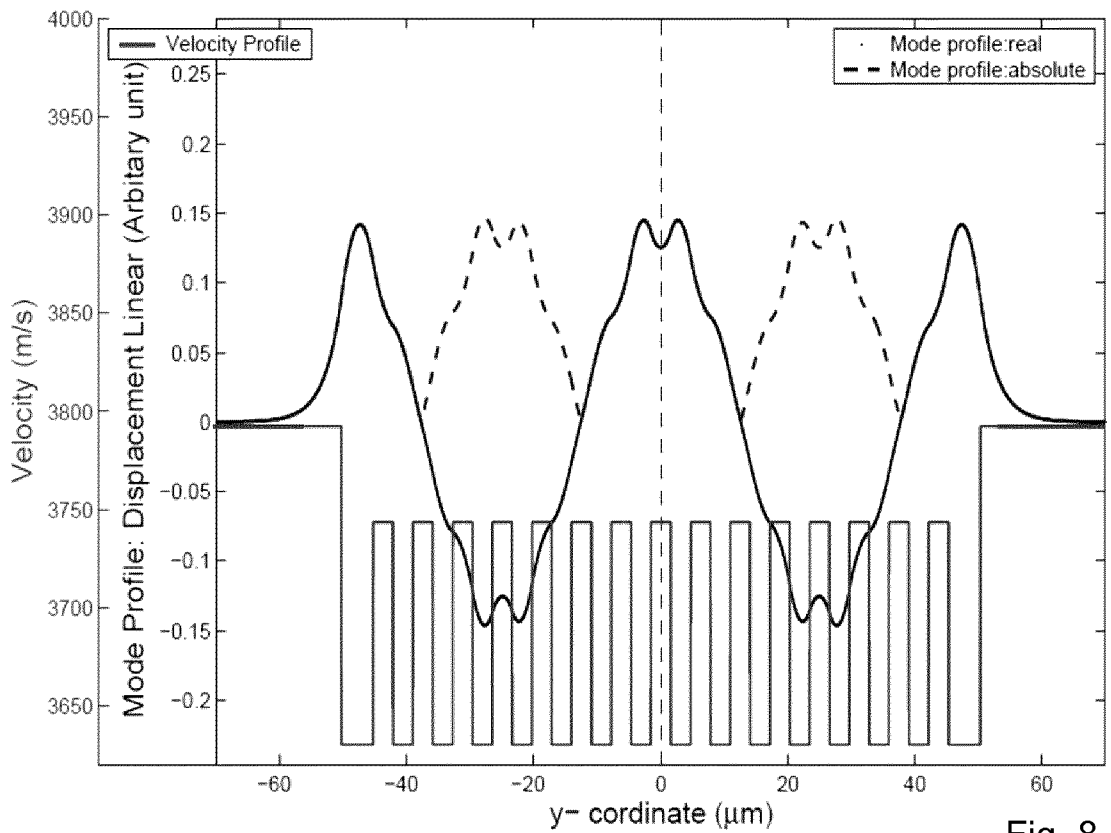


Fig. 8

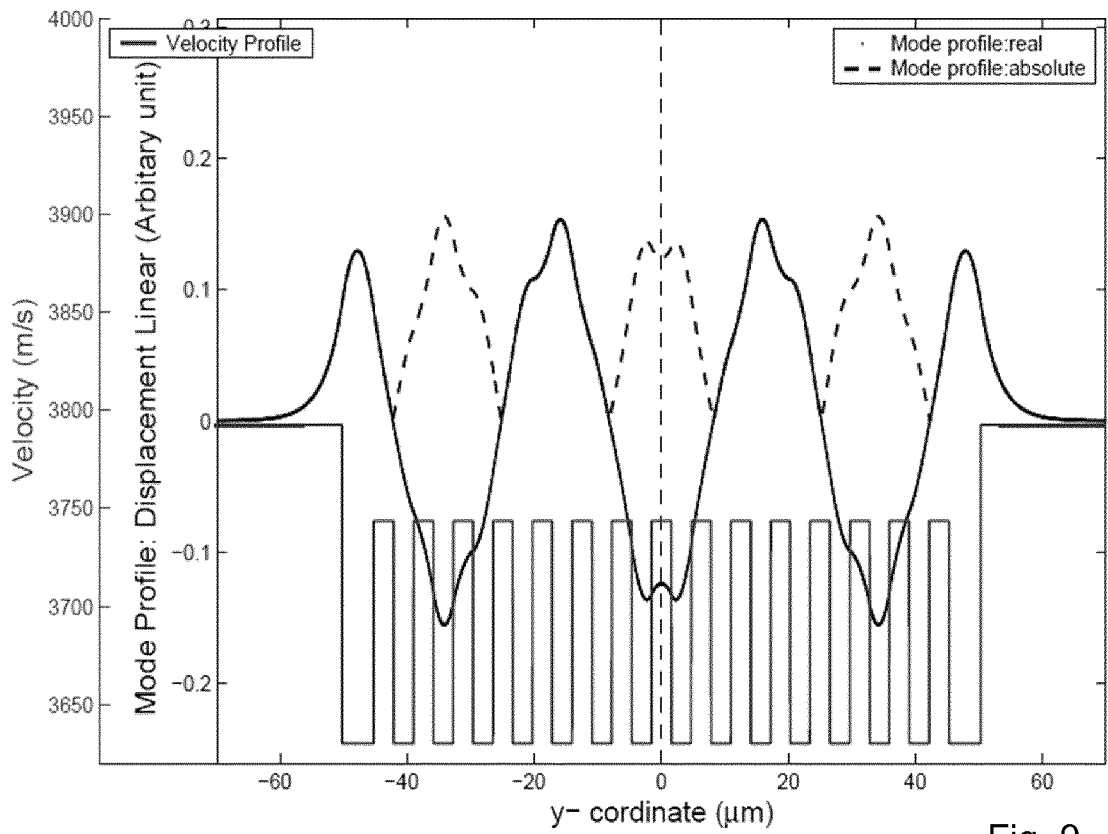


Fig. 9

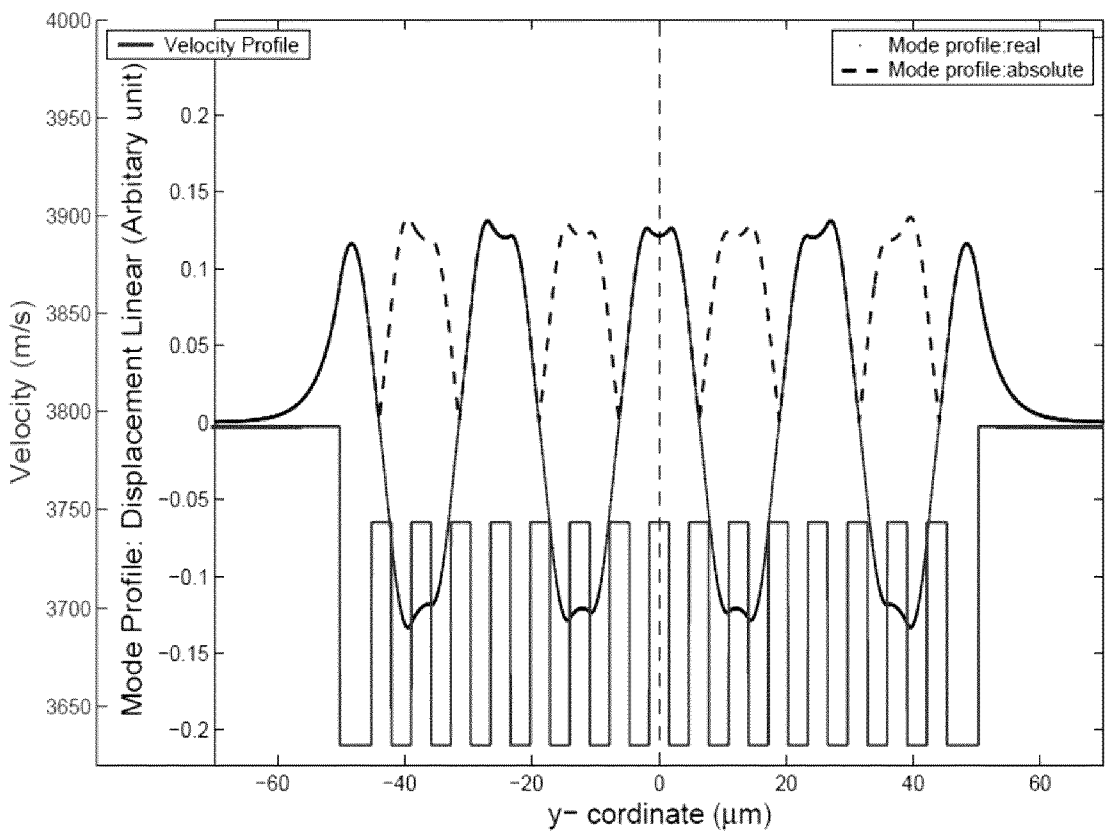


Fig. 10

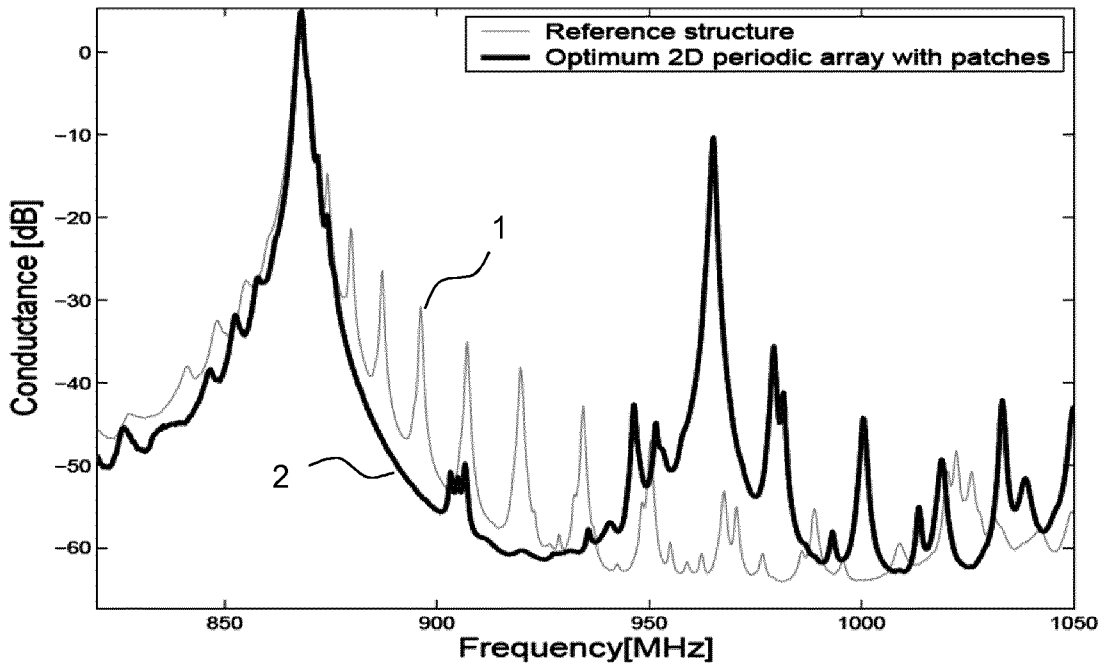


Fig. 11

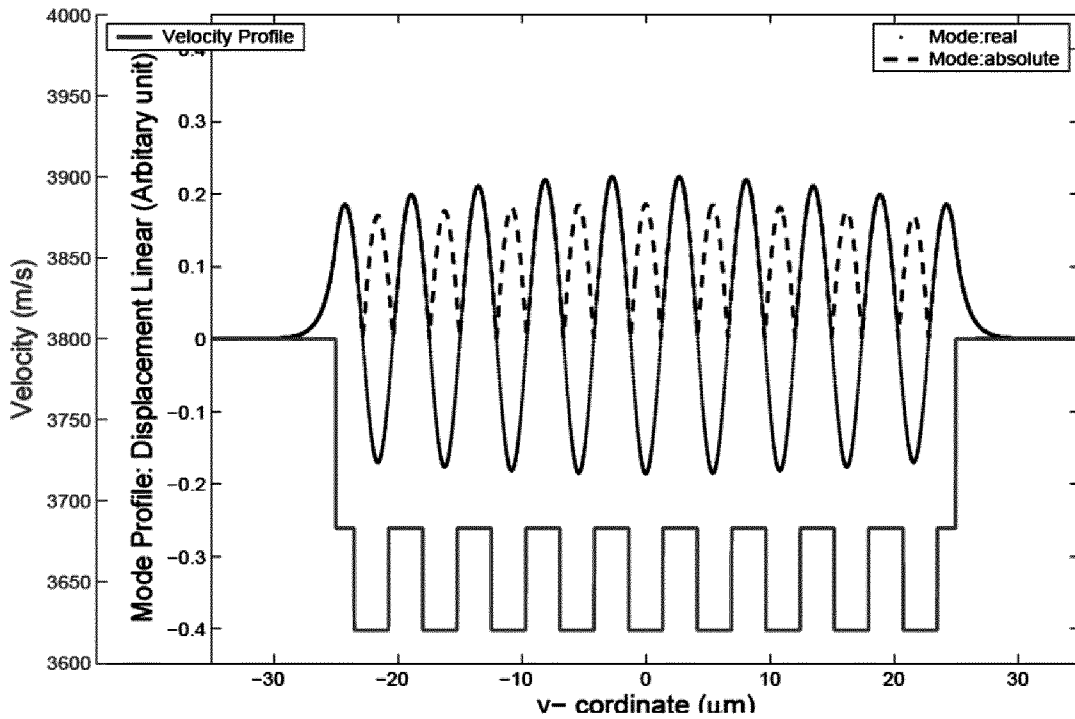


Fig. 12

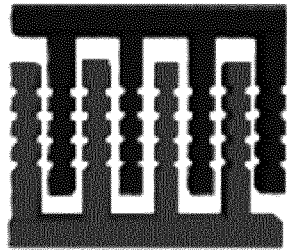


Fig. 13

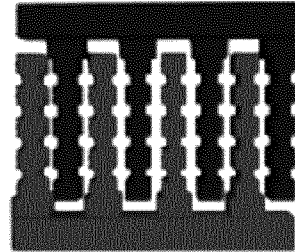


Fig. 14

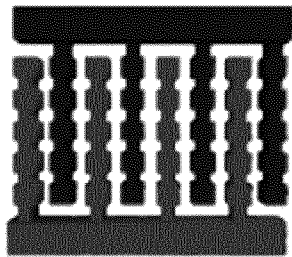


Fig. 15

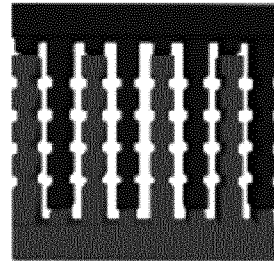


Fig. 16

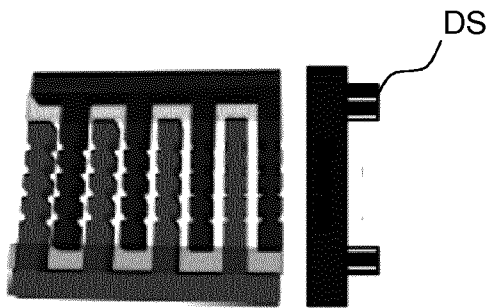


Fig. 17

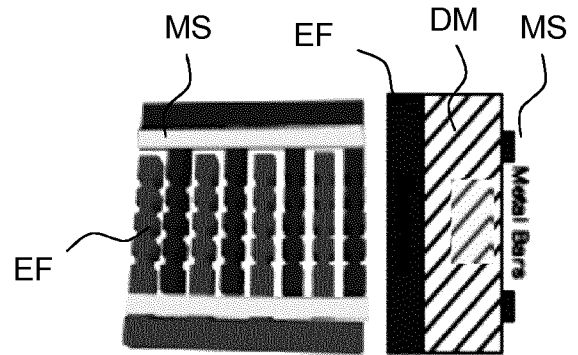


Fig. 18

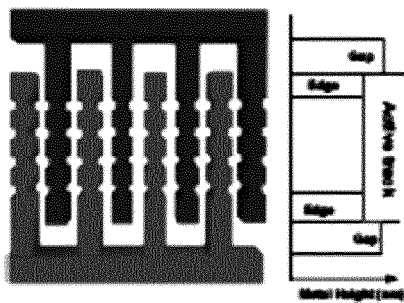


Fig. 19

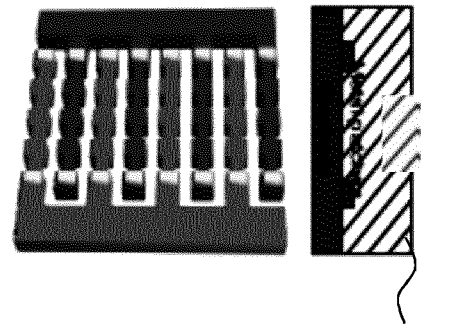


Fig. 20

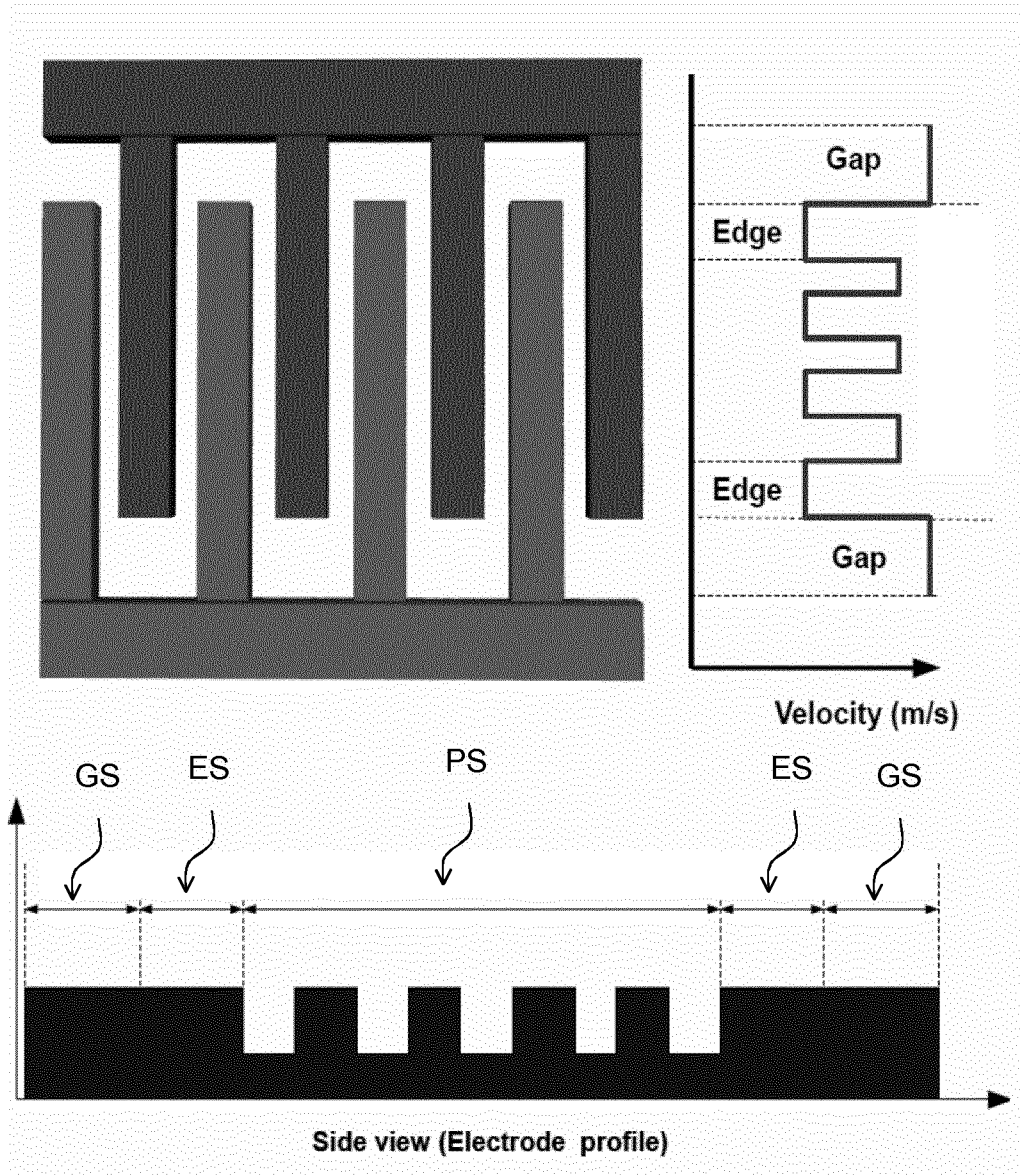


Fig. 21

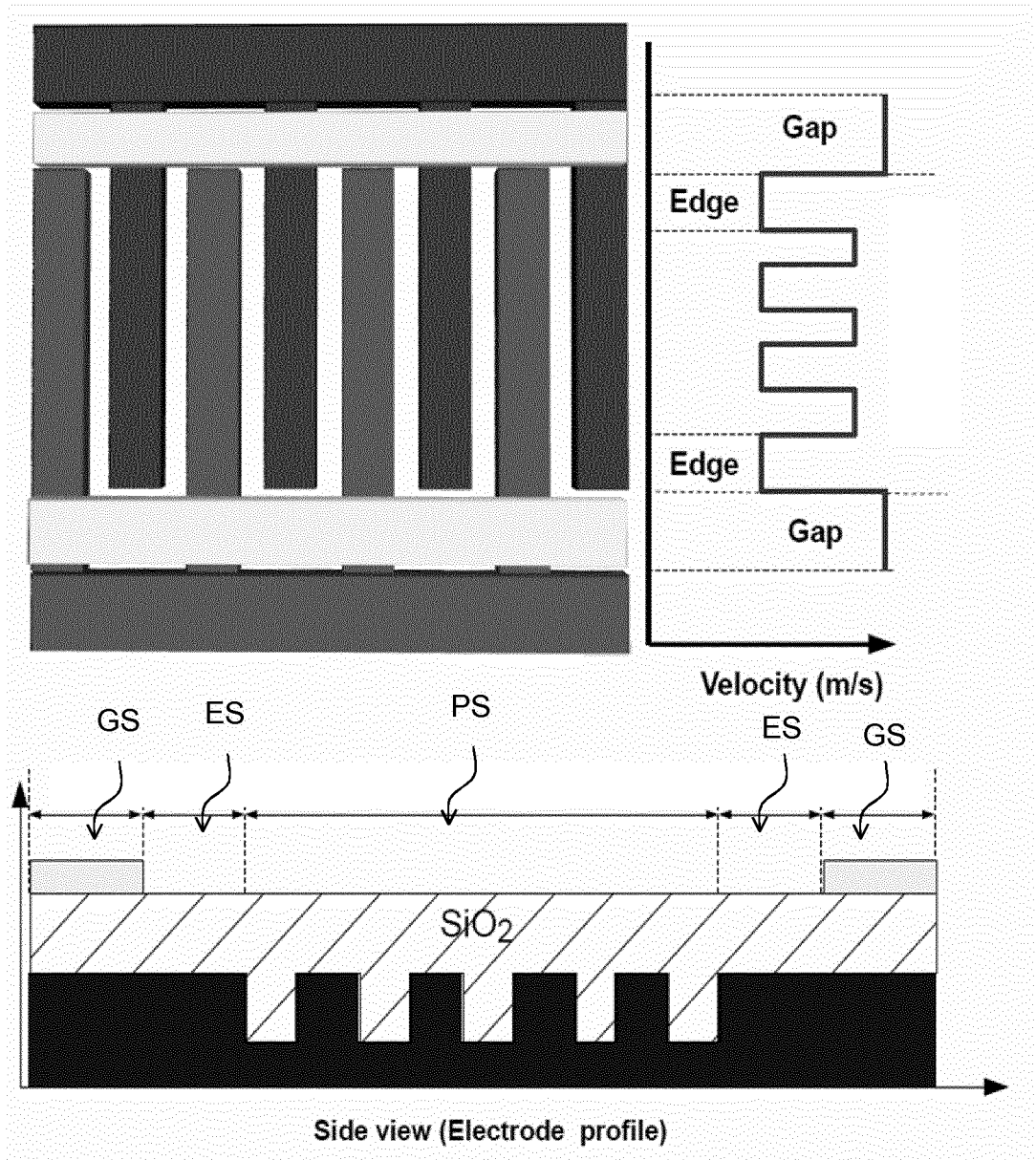


Fig. 22

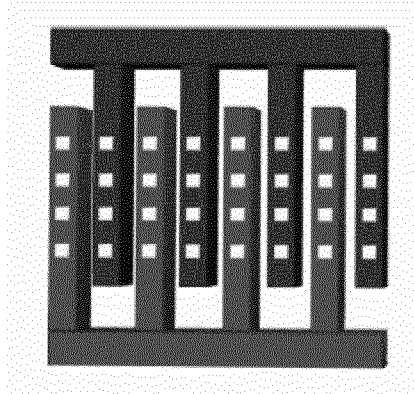


Fig. 23

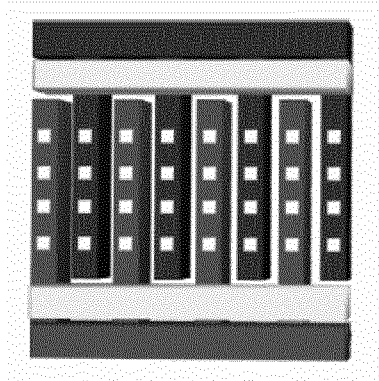


Fig. 24

INTERNATIONAL SEARCH REPORT

International application No
PCT/EP2013/065227

A. CLASSIFICATION OF SUBJECT MATTER
 INV. H03H9/145 H03H9/02
 ADD.
 According to International Patent Classification (IPC) or to both national classification and IPC

B. FIELDS SEARCHED
 Minimum documentation searched (classification system followed by classification symbols)
 H03H
 Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

Electronic data base consulted during the international search (name of data base and, where practicable, search terms used)
 EPO-Internal, WPI Data

C. DOCUMENTS CONSIDERED TO BE RELEVANT		
Category*	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
X	JP S58 83418 A (TOKYO SHIBAURA ELECTRIC CO) 19 May 1983 (1983-05-19) abstract; figure 8 page 106 -----	1,2,4,7, 9-11
Y	US 6 791 236 B1 (ABRAMOV YURI [IL]) 14 September 2004 (2004-09-14) column 6, line 4 - column 7, line 17 column 10, lines 20-23; figure 8 column 10, line 63 - column 11, line 39 -----	1-11
Y	US 2013/051588 A1 (RUILE WERNER [DE] ET AL) 28 February 2013 (2013-02-28) paragraphs [0009] - [0035], [0053], [0066] - [0083], [0089], [0172], [0173]; figures 1-5,8c, 14-25 ----- -/--	1-11

Further documents are listed in the continuation of Box C.

See patent family annex.

* Special categories of cited documents :

<p>"A" document defining the general state of the art which is not considered to be of particular relevance</p> <p>"E" earlier application or patent but published on or after the international filing date</p> <p>"L" document which may throw doubts on priority claim(s) or which is cited to establish the publication date of another citation or other special reason (as specified)</p> <p>"O" document referring to an oral disclosure, use, exhibition or other means</p> <p>"P" document published prior to the international filing date but later than the priority date claimed</p>	<p>"T" later document published after the international filing date or priority date and not in conflict with the application but cited to understand the principle or theory underlying the invention</p> <p>"X" document of particular relevance; the claimed invention cannot be considered novel or cannot be considered to involve an inventive step when the document is taken alone</p> <p>"Y" document of particular relevance; the claimed invention cannot be considered to involve an inventive step when the document is combined with one or more other such documents, such combination being obvious to a person skilled in the art</p> <p>"&" document member of the same patent family</p>
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Date of the actual completion of the international search 19 March 2014	Date of mailing of the international search report 04/04/2014
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Name and mailing address of the ISA/ European Patent Office, P.B. 5818 Patentlaan 2 NL - 2280 HV Rijswijk Tel. (+31-70) 340-2040, Fax: (+31-70) 340-3016	Authorized officer Maget, Judith
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INTERNATIONAL SEARCH REPORT

International application No
PCT/EP2013/065227

C(Continuation). DOCUMENTS CONSIDERED TO BE RELEVANT		
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Y	WO 2012/132238 A1 (PANASONIC CORP [JP]; NAKANISHI HIDEKAZU; NAKAMURA HIROYUKI; TSURUNARI) 4 October 2012 (2012-10-04) paragraphs [0011], [0012], [0028] - [0040]; figures 1,3,8,10, -----	1,3-11
Y	US 2011/068655 A1 (SOLAL MARC [US] ET AL) 24 March 2011 (2011-03-24) paragraphs [0015], [0016], [0050] - [0059], [0063], [0066], [0067], [0076], [0077]; figures 9,10,12,13,17 -----	1,3-11

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